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November 2006

FDS8447

Single N-Channel PowerTrench[®] MOSFET 40V, 12.8A, 10.5m Ω

Features

- Max $r_{DS(on)} = 10.5 m\Omega$ at $V_{GS} = 10 V$, $I_D = 12.8 A$
- Max $r_{DS(on)} = 12.3 \text{m}\Omega$ at $V_{GS} = 4.5 \text{V}$, $I_D = 11.4 \text{A}$
- Low gate charge
- High performance trench technology for extremely low r_{DS(on)}
- High power and current handling capability
- RoHS compliant

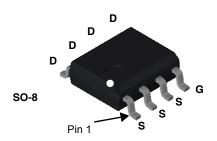


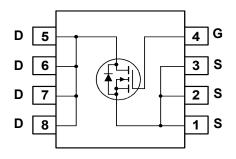
General Description

This single N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Applications

■ DC - DC conversion





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V_{DS}	Drain to Source Voltage		40	V
V_{GS}	Gate to Source Voltage		±20	V
I _D	Drain Current -Continuous	(Note 1a)	12.8	۸
	-Pulsed		50	- A
E _{AS}	Drain-Source Avalanche Energy	(Note 3)	150	mJ
P_{D}	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to 150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance-Single operation, Junction to Ambient	(Note 1a)	50	0000
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS8447	FDS8447	13"	12mm	2500 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

	Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
(Off Chara	cteristics					
	BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40			V
-	ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, referenced to 25°C		34		mV/°C
i	laco	Zero Gate Voltage Drain Current	$V_{DS} = 32V, V_{GS} = 0V$			1	μΑ
	IDSS	Zero Gate Voltage Drain Gurrent	T _J = 55°C			10	μΑ
	I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250μA, referenced to 25°C		-5		mV/°C
		$V_{GS} = 10V, I_D = 12.8A$		9	10.5	
r _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 11.4A$		10	12.3	mΩ
		$V_{GS} = 10V, I_D = 12.8A, T_J = 125^{\circ}C$		13	15	
9 _{FS}	Forward Transconductance	V _{DS} = 10V, I _D = 12.8A		75.3		S

Dynamic Characteristics

	C _{iss}	Input Capacitance	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	2000	2600	pF
ĺ	C _{oss}	Output Capacitance		250	350	pF
ĺ	C _{rss}	Reverse Transfer Capacitance	T - TIVILIZ	150	250	pF
	R_g	Gate Resistance	f = 1MHz	1.3		Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		11	20	ns
t _r	Rise Time	$V_{DD} = 20V, I_{D} = 12.8A$ $V_{GS} = 10V, R_{GEN} = 4.5\Omega$	14	25	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = 10V, R _{GEN} = 4.5Ω	27	42	ns
t _f	Fall Time		7	14	ns
Q_g	Total Gate Charge at V _{GS} = 10V		35	49	nC
Q_g	Total Gate Charge at V _{GS} = 5V	$V_{DS} = 20V, I_{D} = 12.8A,$	19	27	nC
Q _{gs}	Gate to Source Gate Charge		6		nC
Q_{gd}	Gate to Drain "Miller" Charge		7		nC

Drain-Source Diode Characteristics and Maximum Ratings

V_{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0V, I _S = 12.8A (note 2)	0.84	1.2	V
t _{rr}	Reverse Recovery Time	I _F = 12.8A, d _{iF} /d _t = 100A/μs	19	29	ns
Q _{rr}	Reverse Recovery Charge	T _F = 12.6A, α _{iF} /α _t = 100A/μS	9.5	19	nC

Notes

1: R_{0JA} is the sum of the junction-to-case and case-to- ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.



 a) 50°C/W when mounted on a 1in² pad of 2 oz copper

Scale 1:1 on letter size paper



b) 125°C/W when mounted on a minimum pad .

- 2: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%.
- 3: Starting $T_J = 25^{\circ}C$, L = 3mH, $I_{AS} = 10A$, $V_{DD} = 40V$, $V_{GS} = 10V$.

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

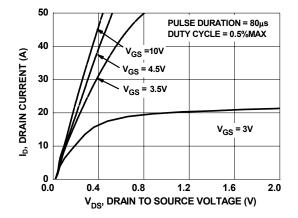


Figure 1. On Region Characteristics

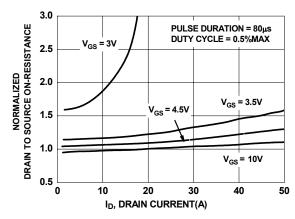


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

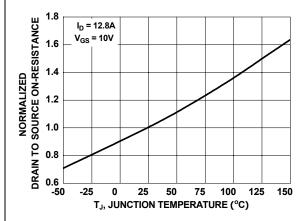


Figure 3. Normalized On Resistance vs Junction Temperature

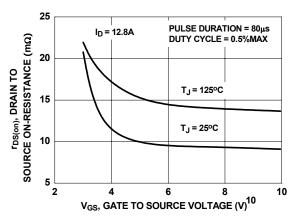


Figure 4. On-Resistance vs Gate to Source Voltage

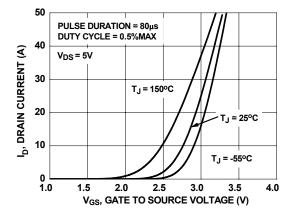


Figure 5. Transfer Characteristics

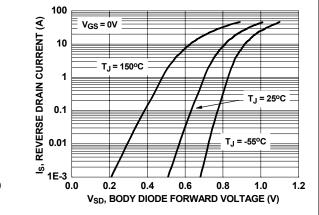


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

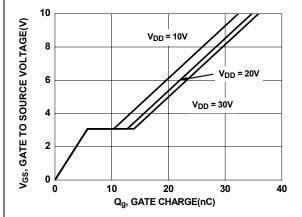


Figure 7. Gate Charge Characteristics

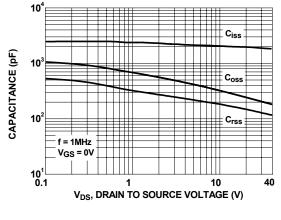


Figure 8. Capacitance vs Drain to Source Voltage

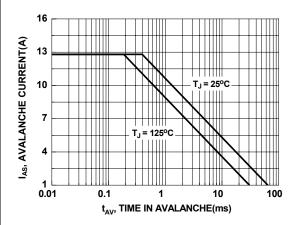


Figure 9. Unclamped Inductive Switching Capability

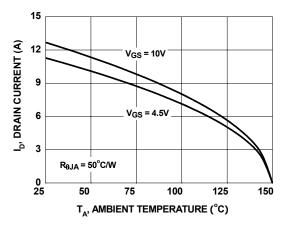


Figure 10. Maximum Continuous Drain Current vs
Ambient Temperature

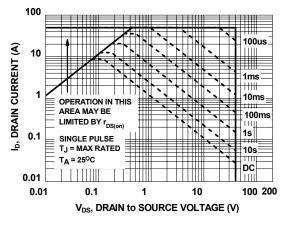


Figure 11. Forward Bias Safe Operating Area

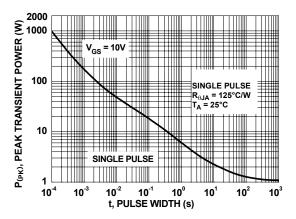


Figure 12. Single Pulse Maximum Power Dissipation

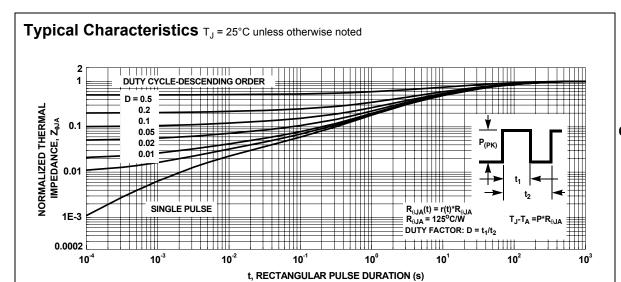


Figure 13. Transient Thermal Response Curve



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